ADE-208-111C(Z)

HSM126S
Silicon Schottky Barrier Diode for System Protection

HITACHI

Rev. 3
May. 1995

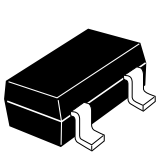
Features

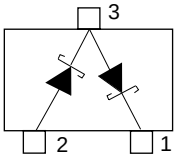
- HSM126S which is connected in series configuration enable to protect electric systems from miss-operation against external + and – surge.
- Low V_F and low leakage current.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Mark	Package Code
HSM126S	S14	MPAK

Pin Arrangement





(Top View)

1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

Absolute Maximum Ratings (Ta = 25°C) ***

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	I_o *	200	mA
Non-Repetitive peak forward surge current	I_{FSM} **	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

* Sine wave, Two device total
** 50Hz half sine wave 1 pulse
*** Per one device

Electrical Characteristics (Ta = 25°C) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	2.0	µA	V_R = 5 V
Forward voltage	V_F	—	—	0.35	V	I_F = 10 mA
Capacitance	C	—	40	—	pF	V_R= 0 V, f = 1 MHz

* Per one device

HSM126S

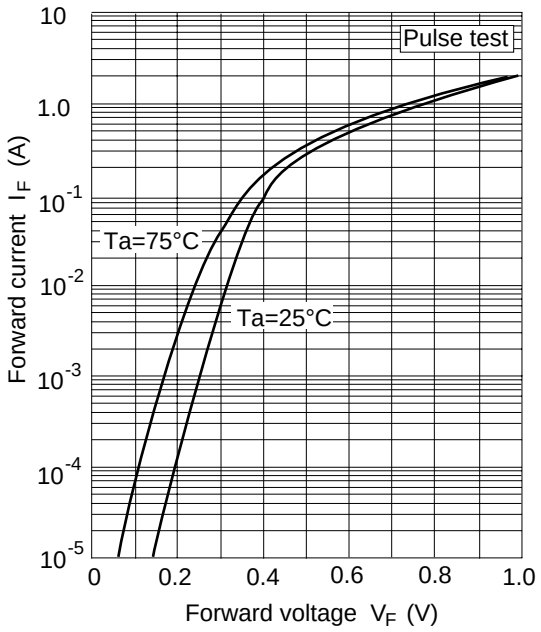


Fig.1 Forward current Vs. Forward voltage

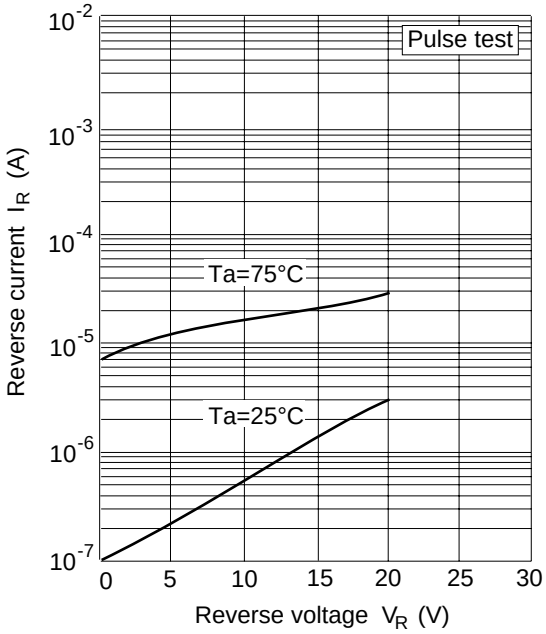


Fig.2 Reverse current Vs. Reverse voltage

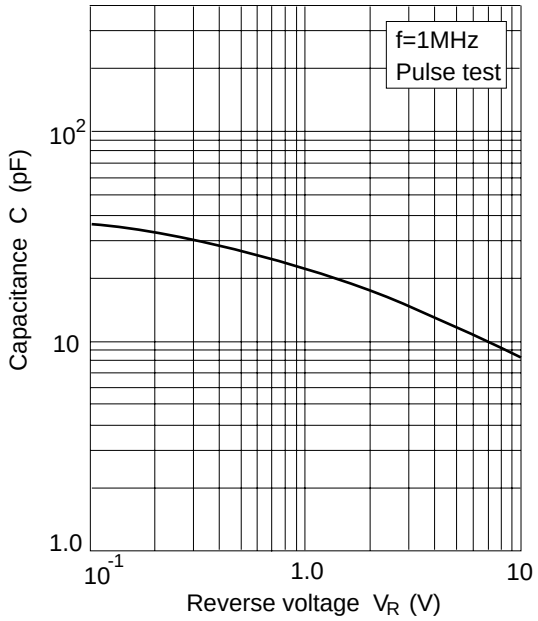
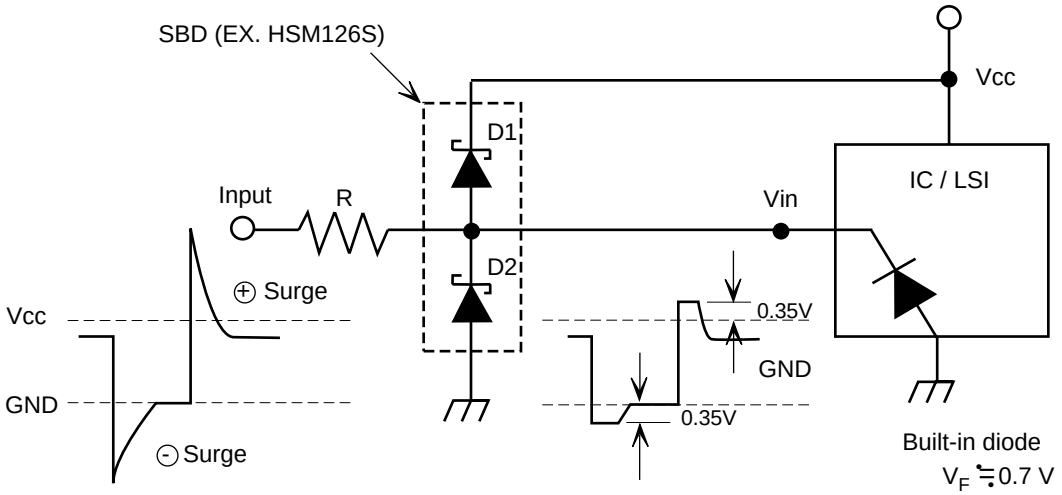


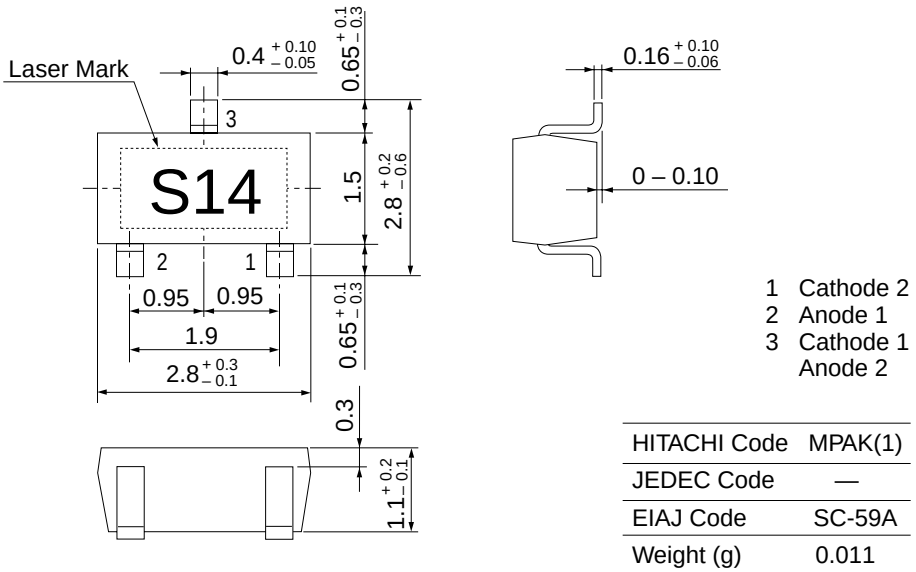
Fig.3 Capacitance Vs. Reverse voltage

Example of application circuite



Package Dimensions

Unit: mm



1 Cathode 2
2 Anode 1
3 Cathode 1
Anode 2

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011